

FEATURES

| $V_{DS} = 60V, I_D = 50A$

| $R_{DS(ON) Typ} = 12.5m\Omega @ V_{GS} = 10V$

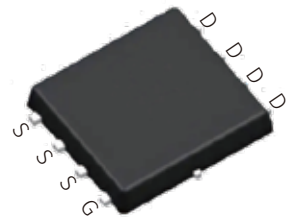
| $R_{DS(ON) Typ} = 15.5m\Omega @ V_{GS} = 4.5V$

| Advanced Trench Technology

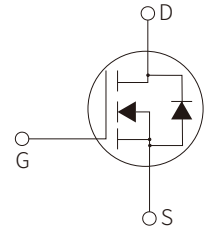
| Excellent $R_{DS(ON)}$ and Low Gate Charge

| 100% UIS TESTED!

| 100% ΔV_{ds} TESTED!



PDFN3×3-8L



Schematic Symbol

APPLICATION

| Load Switch

| PWM Application

| Power Management

APPROVALS

RoHS Compliance with 2011/65/EU

HF Compliance with IEC61249-2-21:2003

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	60	V
Pulsed Drain Current ⁽¹⁾	I_{DM}	200	A
Continuous Drain Current	I_D	$T_c = 25^\circ C$	50
		$T_c = 100^\circ C$	30
Power Dissipation $T_c = 25^\circ C$	P_D	48	W
Gate-to-Source Voltage	V_{GS}	± 20	V
Single Pulsed Avalanche Energy ⁽²⁾	E_{AS}	36	mJ
Junction & Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ C$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.6	$^\circ C/W$

ELECTRICAL CHARACTERISTICS (T_A=25°C)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250μA	60			V
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V			1.0	μA
On Characteristics						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.0	1.3	1.8	V
Static Drain-Source ON-Resistance ²	R _{DS(on)}	V _{GS} =10V, I _D =20A		12.5	15	mΩ
		V _{GS} =4.5V, I _D =10A		15.5	19	mΩ
Dynamic Characteristics						
Input capacitance	C _{iss}	V _{GS} =0V, V _{DS} =30V, f = 1MHz		590		pF
Output capacitance	C _{oss}			210		pF
Reverse transfer capacitance	C _{rss}			10		pF
Total Gate Charge	Q _g	V _{DS} =30V, V _{GS} =0 to 10V I _D =20A		13.9		nC
Gate-Source Charge	Q _{gs}			1.6		nC
Gate Drain ("Miller") Charge	Q _{gd}			3.1		nC
Switching Characteristics						
Turn-on Delay Time	t _{d(on)}	V _{DD} =30V, V _{GS} =10V R _{GEN} =6Ω, I _D =20A		3.7		nS
Turn-on Rise Time	t _r			4.3		nS
Turn-Off Delay Time	t _{d(off)}			16.2		nS
Turn-Off Fall Time	t _f			6.5		nS
Drain-Source Diode Characteristics and Max Ratings						
Drain to Source Diode Forward Voltage	V _{SD}	I _S =20A, V _{GS} =0V			1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F =15A di/dt = 100A/us		24		nS
Body Diode Reverse Recovery Charge	Q _{rr}			9.3		nC
Maximum Continuous Drain to Source Diode Forward Current	I _S				50	A
Maximum Pulsed Drain to Source Diode Forward Current	I _{SM}				200	A

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. E_{AS} condition: Starting T_J=25°C, V_{DD}=30V, V_G=10V, R_G=25ohm, L=0.5mH, I_{AS}=12A
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 0.5%

PARAMETER CHARACTERISTIC CURVE

Fig 1: Output Characteristics

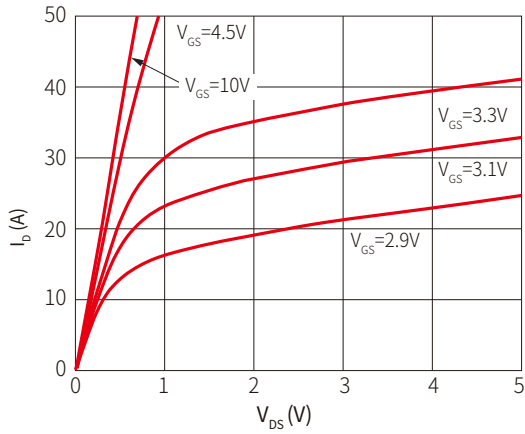


Figure 2: Typical Transfer Characteristics

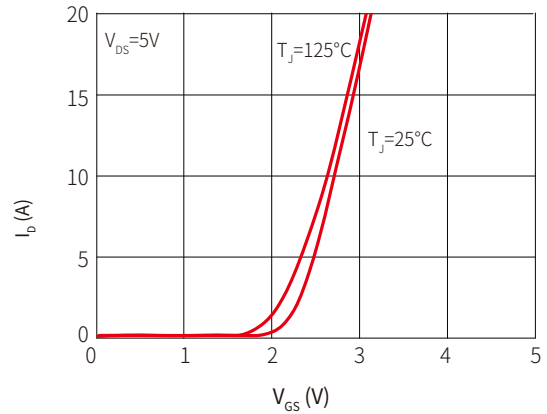


Figure 3: On-Resistance vs. Drain Current

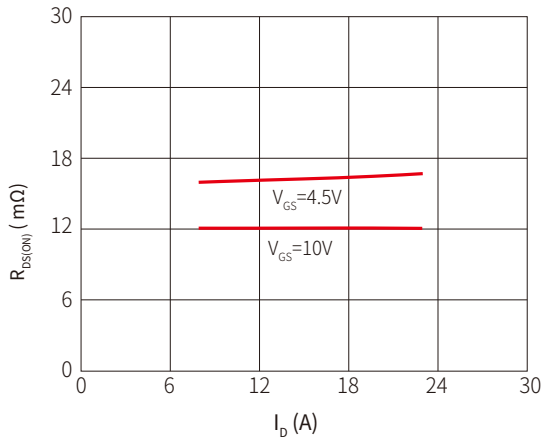


Figure 4: Body Diode Characteristics

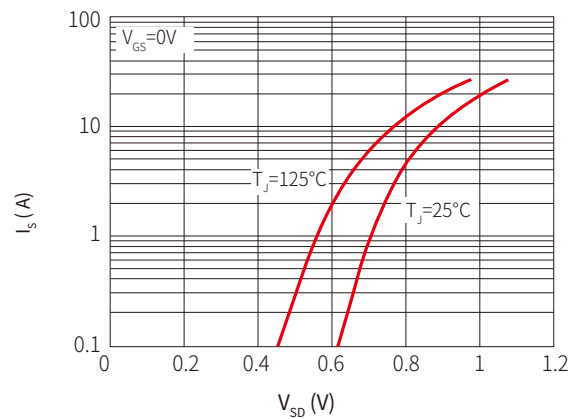


Figure 5: Gate Charge Characteristics

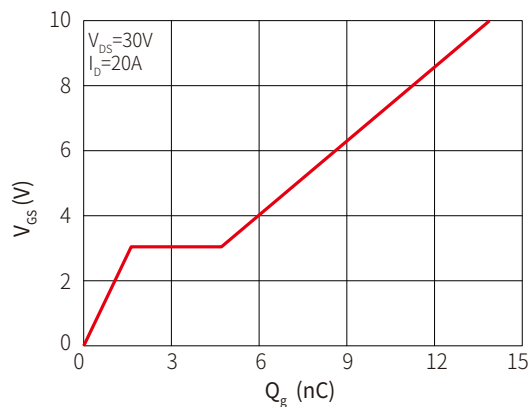


Figure 6: Capacitance Characteristics

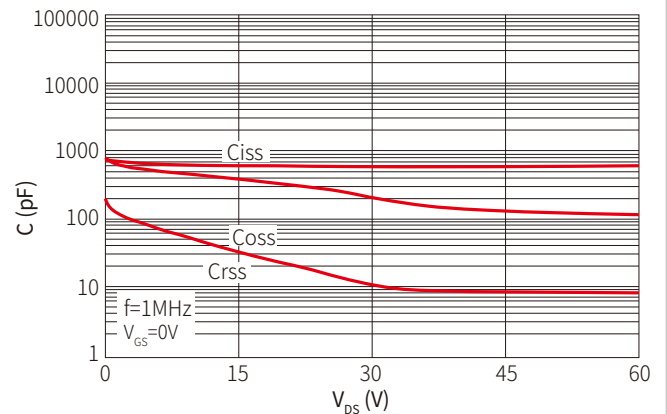


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

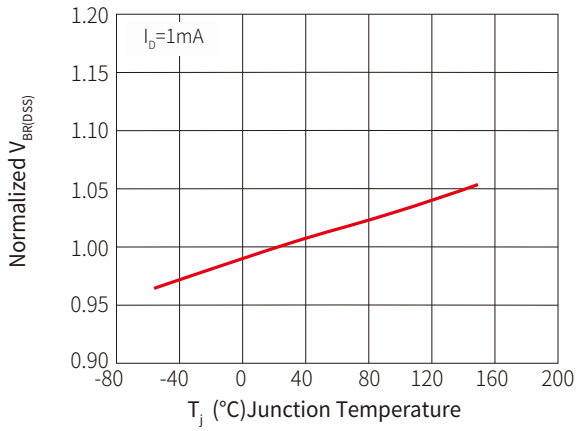


Figure 8: Normalized on Resistance vs. Junction Temperature

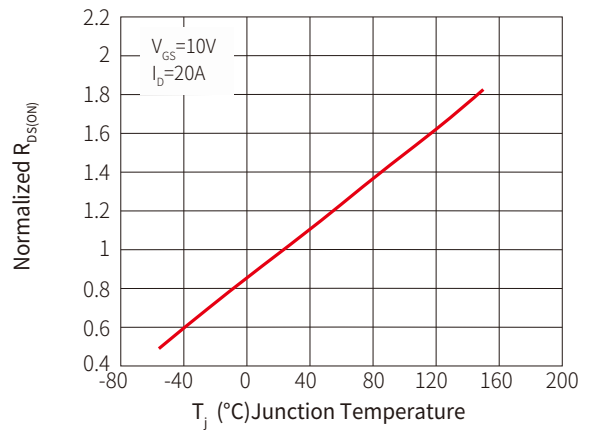


Figure 9: Maximum Safe Operating Area

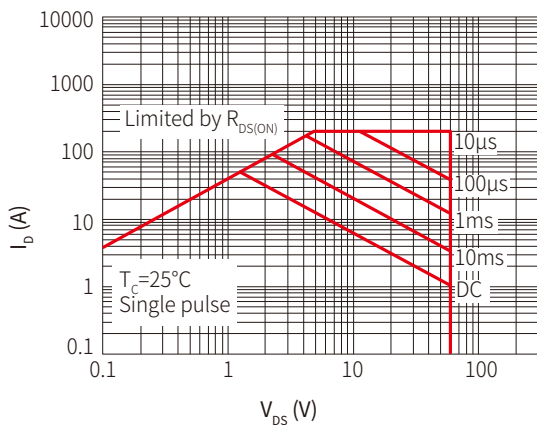


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

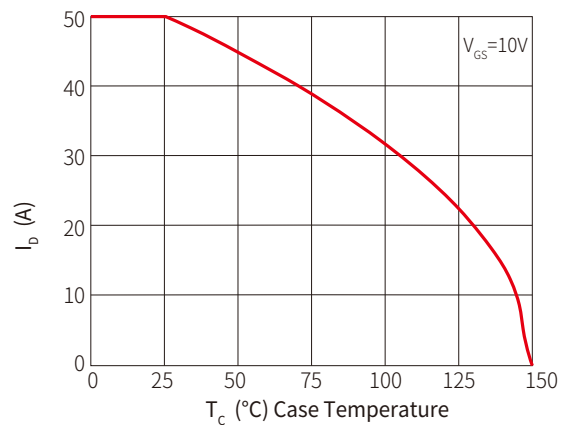
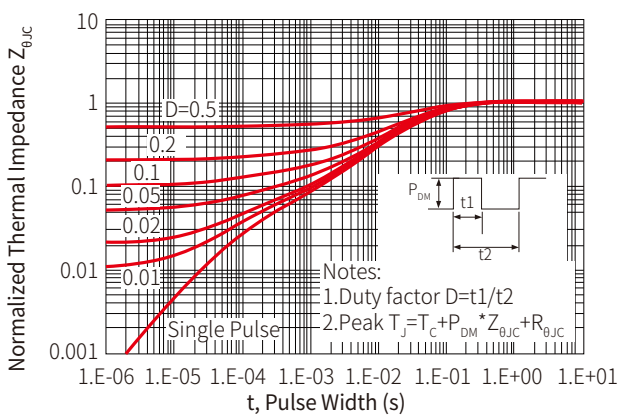
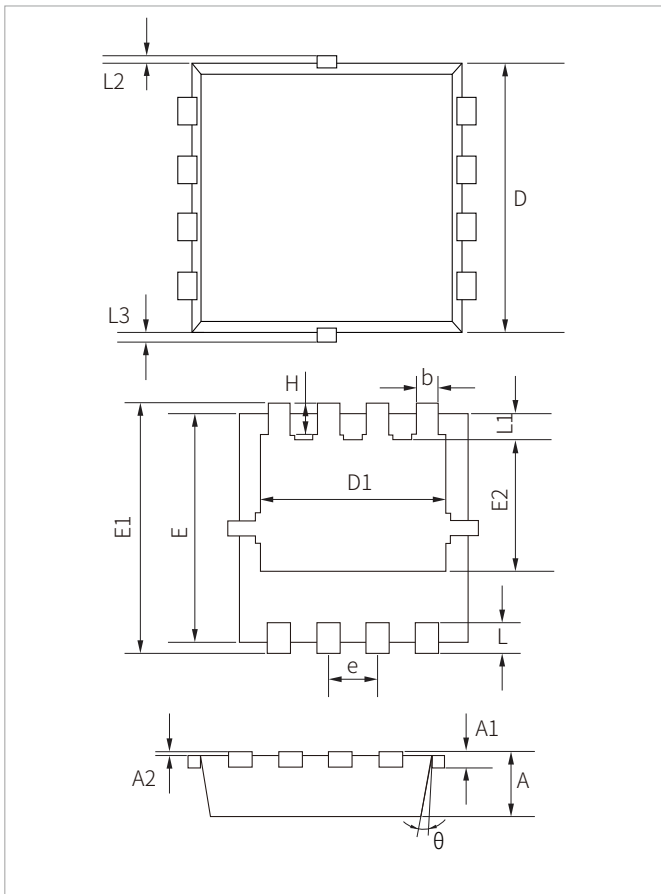


Figure 11: Normalized Maximum Transient Thermal Impedance




PDFN3x3-8L PACKAGE INFORMATION



Ref.	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	0.650	0.850	0.026	0.033
A1	0.152REF		0.006REF	
A2	0~0.05		0~0.002	
D	2.900	3.300	0.114	0.130
D1	2.250	2.650	0.089	0.104
E	2.900	3.300	0.114	0.130
E1	3.150	3.550	0.124	0.140
E2	1.535	1.935	0.060	0.076
b	0.200	0.400	0.008	0.016
e	0.550	0.750	0.022	0.030
L	0.300	0.500	0.012	0.020
L1	0.180	0.480	0.007	0.019
L2	0~0.100		0~0.004	
L3	0~0.100		0~0.004	
H	0.315	0.515	0.012	0.020
θ	9°	13°	9°	13°

ORDERING INFORMATION

Part Number	Component Package	Marking	QTY/Reel	Reel Size
SNM0612Q	PDFN3×3-8L	 0612 XXXX	5000PCS	13"

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